



THE DATASHEET OF BCP55TA

SOT223 NPN SILICON PLASMA
MEDIUM POWER TRANSISTOR
ISSUE 3 – AUGUST 1995

FEATURES

- * Suitable for AF drivers and output stages
- * High collector current and Low $V_{CE(sat)}$

COMPLEMENTARY TYPE – BCP52

PARTMARKING DETAILS – BCP55
BCP55 – 100 mW
BCP55 – 100 mW

ABSOLUTE MAXIMUM RATINGS

PARAMETER
Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Peak Pulse Current
Continuous Collector Current
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$
Operating and Storage Temperature Range

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	MIN	MAX
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	60	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	
Collector Cut-Off Current	I_{CBO}		
Emitter Cut-Off Current	I_{EBO}		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		
Static Forward Current Transfer Ratio	h_{FE}	40	250
	BCP55-10	63	
	BCP55-16	10	
Transition Frequency	f_T		

*Measured under pulsed conditions. Pulse width 100 μs, duty cycle 10%.

Looking for pricing, stock, or lifecycle information?

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